Epson Timing Devices

HIGH-STABILITY G-SERIES TCXOS

Industry's Best Stability. DoubleSealTM Technology.

Epson G-SERIES TCXOs & VC-TCXOs

■ Temperature Stability: < ±100 ppb -40 to +85 °C

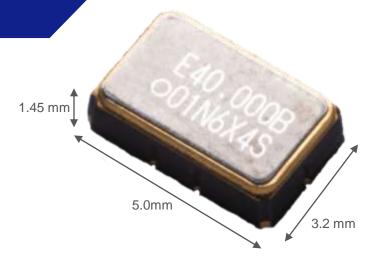
■ Short-Term Stability: 2e-10@ 1s root Allan variance

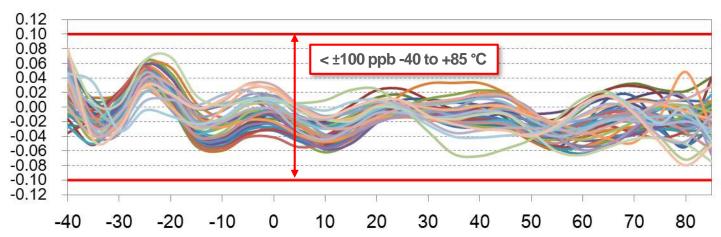
■ **Holdover:** < ±10 ppb over 24 hours

Frequency Range: 10-40 MHz

Single-Ended Output: LVCMOS or clipped sine

• **Size:** 5.0 x 3.2 x 1.45





Designed for network synchronization, small cell, and microwave radio applications, Epson's G-series TCXOs deliver superior stability to support all the latest networking standards and requirements.

In addition to $< \pm 100$ ppb Temperature stability, Epson's G-series TCXOs achieve the industry's leading wander, short-term stability, environmental isolation, and airflow isolation.

Epson's G-series TCXOs comply with all the latest networking standards from 3GPP and IEEE-1588 to ITU-T packet clock drafts and recommendations.



Epson G-SERIES TCXOS



Epson's G-series TCXOs are designed to provide the ultimate in stability for synchronization applications. With ± 100 ppb temperature stability, 2e-10@ 1s root Allan variance, and $< \pm 10$ ppb 24-hour holdover, Epson's G-series TCXOs are the industry's most stable TCXOs.

Temperature Stability:

With cut-angle and geometry-optimized crystal design, individual factory calibration, and a proprietary fitting-error reduction algorithm, Epson's G-series TCXOs are accurate to better than ± 100 ppb from -40 to +85 °C, meeting 3GPP medium-range specifications for indoor and outdoor systems.

Short-Term Stability:

Photolithographic crystal processing allows Epson TCXOs to deliver better wander and short-term stability than competing mechanical designs. Epson's G-series TCXOs achieve root Allan variance of 2e-10@ 1s which improves synchronization performance for systems using IEEE-1588 and emerging packet timing standards.

ADVANTAGES

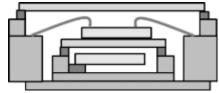
- Tight temperature stability < ± 100 ppb
- Superior short-term stability and wander
- G.8262 EEC-1 and EEC-2 compliant holdover
- Extended temperature range
- Airflow isolation and environmental immunity from patented DoubleSeal™ technology
- Full standards compliance

Holdover:

Reduced lattice-strain crystal technology allows Epson's G-series TCXOs to deliver superior drift and aging, achieving < ±10 ppb over 24 hours which meets G.8262 EEC 1 and 2 holdover requirements and provides wide margin to GR-1244 Stratum 3.

DoubleSeal™ Technology:

Epson's G-series TCXOs employ patented DoubleSeal™ technology to isolate the crystal and temperature sensor from external environmental conditions. As a result, frequency and phase are protected from airflow, temperature gradients, and turbulence.



DoubleSeal™ Technology

Still air is an unrealistic assumption for networking equipment. Even minimal airflow can degrade wander and stability. For outdoor equipment or equipment with cooling fans and/or nearby hot components, Epson G-series TCXOs are far more stable than conventional TCXOs.

Standards Compliance:

Airflow Performance:

As an active member of ITU-T, Epson contributes to emerging networking standards and is up-to-date on all the latest requirements. Epson's G-series TCXOs comply with multiple wireless and wireline standards, including:

- Wireless: 3GPP LTE Local-Area and Medium-Range
- SONET BITS/SETS: GR-1244-CORE Stratum 3
- Packet Timing (Network Sync.): G.8262 EEC-1 & EEC-2 Epson G-series TCXOs provide large margin to MTIE specifications for multiple standards.

MTIE @ 25 °C 0.1 Hz GR-1244-CORE G.8262 EEC-1 G.8262 EEC-2 > 25x margin Epson G-series TCXO

Configuration & Options:

Epson's G-series TCXOs cover a frequency range of 10-40 MHz. Options include VC-TCXO or TCXO, LVCMOS or clipped-sine wave outputs, an optional Temperature sensor output, and 3 stability ranges: ±100, ±250, and ±280 ppb.

Product	Size (mm x mm x mm)	Outputs	I _{DD} @ 3.3V	Frequency	Stability -40 to +85 °C
TG5032CGN	5.3 x 3.2 x 1.45	LVCMOS	3.5 mA typ., < 6 mA max	10-40 MHz	±100, ±250, or ±280 ppb
TG5032SGN	5.3 x 3.2 x 1.45	Clipped sine	2 mA typ., < 5 mA max	10-40 MHz	±100, ±250, or ±280 ppb

